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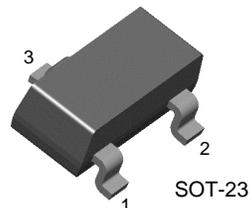
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KSA1298

KSA1298

Low Frequency Power Amplifier

- Complement to KSC3265



1. Base 2. Emitter 3. Collector

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{CB0}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-800	mA
I_B	Base Current	-160	mA
P_C	Collector Power Dissipation	200	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-55 ~ 150	$^\circ\text{C}$

• Refer to KSA643 for graphs.

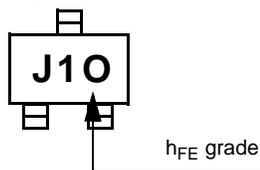
Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}, I_B = 0$	-25			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = -1\text{mA}, I_C = 0$	-5			V
I_{CBO}	Collector Cut-off Current	$V_{CB} = -30\text{V}, I_E = 0$			-100	nA
I_{EBO}	Emitter Cut-off Current	$V_{BE} = -5\text{V}, I_C = 0$			-100	nA
h_{FE1} h_{FE2}	DC Current Gain	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$ $V_{CE} = -1\text{V}, I_C = -800\text{mA}$	100 40		320	
$V_{CE}(\text{sat})$	Collector-Emitter Saturation Voltage	$I_C = -500\text{mA}, I_B = -20\text{mA}$			-0.4	V
$V_{BE}(\text{on})$	Base-Emitter On Voltage	$V_{CE} = -1\text{V}, I_C = -10\text{mA}$	-0.5		-0.8	V
f_T	Current Gain Bandwidth Product	$V_{CE} = -5\text{V}, I_C = -10\text{mA}$		120		MHz
C_{ob}	Output Capacitance	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		13		pF

h_{FE1} Classification

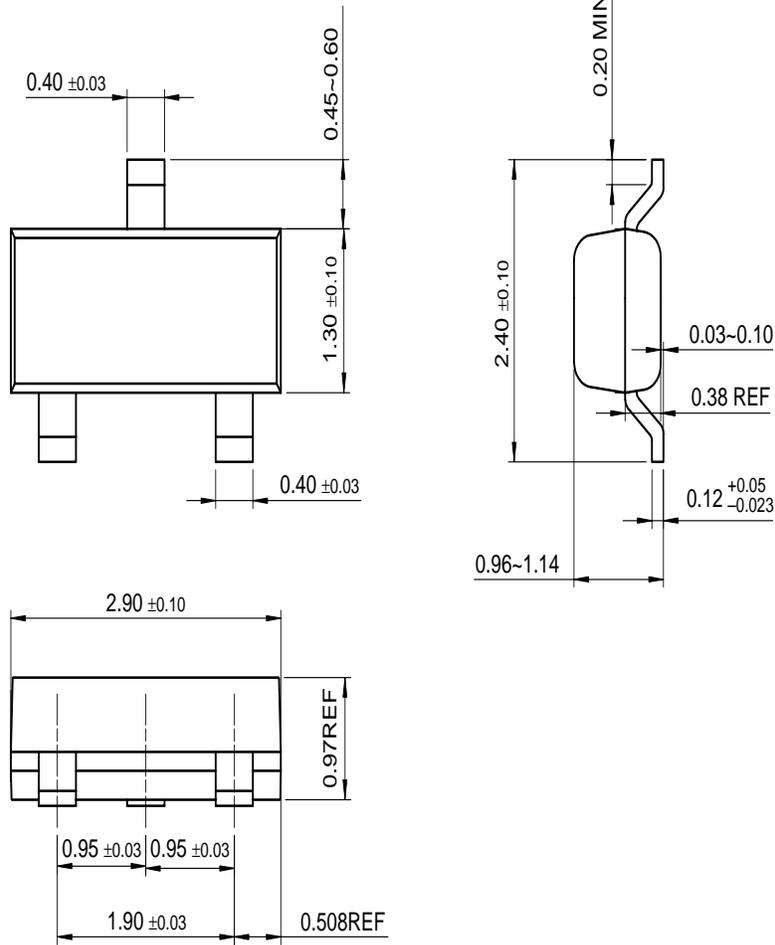
Classification	O	Y
h_{FE1}	100 ~ 200	160 ~ 320

Marking



Package Dimensions

SOT-23



Dimensions in Millimeters